TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIII)

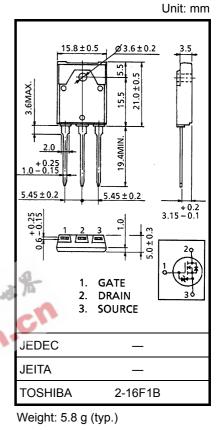
2SK2606

DC–DC Converter, Relay Drive and Motor Drive Applications

- Low drain-source ON resistance $: RDS(ON) = 1.0 \Omega(typ.)$
- High forward transfer admittance $: |Y_{fs}| = 7.0 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 640 \ V)$
- Enhancement mode : $V_{th} = 2.0 \sim 4.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{ID} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	800	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	800	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	8	А	
	Pulse (Note 1)	I _{DP}	24	A	
Drain power dissipation (Tc = 25°C)		PD	85	W	
Single pulse avalanche energy (Note 2)		E _{AS}	883	mJ	21
Avalanche current		I _{AR}	8	A	
Repetitive avalanche energy (Note 3)		E _{AR}	8.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch−c)}	1.47	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	41.6	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 25.0 mH, I_{AR} = 8 A, R_G = 25 Ω

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

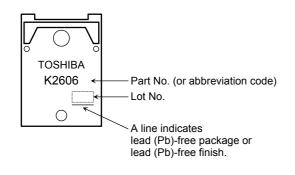
Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±10	μA
Gate-source bre	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 640 V, V _{GS} = 0 V	_		100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	800	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0		4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 4 A,	_	1.0	1.2	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 15 V, I _D = 4 A	3.0	7.0	_	S
Input capacitance	capacitance C _{iss}		_	2160	_		
Reverse transfer capacitance		C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		45	_	pF
Output capacitance		C _{oss}			200	_	
Switching time	Rise time	tr	$V_{GS} \stackrel{10V}{_{0V}} \prod_{\substack{D=4.0A \\ \downarrow} \\ \downarrow} R_{L} = 100\Omega$	_	25	_	
	Turn-on time	t _{on}		_	60	_	- ns
	Fall time	t _f		_	25	_	
	Turn-off time	t _{off}	$v_{DD} = 400 v$ Duty $\leq 1\%$, t _w = 10 µs	2	110	_	
Total gate charge (gate-source plus gate-drain)		Qg	i i i om.		68	_	_
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 8 A	_	38	_	nC
Gate-drain ("miller") Charge		Q _{gd}		_	30	_	

Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	8	А
Pulse drain reverse current (Note 1)	IDRP	_	_	_	24	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 8 A, V _{GS} = 0 V	_	_	-1.9	V
Reverse recovery time	t _{rr}	I _{DR} = 8 A, V _{GS} = 0 V, dI _{DR} / dt = 100 A / µs		1500	_	ns
Reverse recovery charge	Q _{rr}	1DR = 0 A, VGS = 0 V, UDR / 01 = 100 A / ps		19	—	μC

Marking



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20070701-EN

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